Measurements of Lorentz angle in irradiated silicon strip sensors

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principle of measurement



- •charge carriers are produced at a strip
- •Lateral drift in magnetic field is measured
- •Lorentz angle is calculated

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Hybrid with strip sensor



- double sided sensor (~1cm²),
 50µm pitch, 300µm thickness,
 strips on both sides parallel
 (former sensors had stripes crossed)
- bias resistors (10M Ω) on hybrid
- Premux128 Chip for data recording
- irradiated with 26MeV protons
- Φ =6 x 10¹³ and Φ =1,2 x 10¹⁴

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measurement setup



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Measured signals









lorentzshift of holes with different temperatures





Lorentzshift with red and infrared laser for 258K



Electrons and holes over temperature



lorentzshift with temperature



Lorentzshift of electons for red and infrared laser after irradiation

Lorentzshift red vs. Infrared laser after irradiation T=258K



Lorentzshift of electrons for different fluences

Lorentzshift of different fluences with red laser



Lorentzshift of holes for different fluences



Lorentzshift of different fluences









summary

- Lorentzangle is affected by radiation and temperature
- Annealing shows no significant effect
- The effects will be significant in future HEP experiments
- More reserch is necessary to make corrections in track reconstruction
- Higher fluences coming soon

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